UNISONIC TECHNOLOGIES CO., LTD

13003DW

Preliminary

NPN SILICON TRANSISTOR

NPN SILICON BIPOLAR TRANSISTORS FOR LOW FREQUENCY AMPLIFICATION

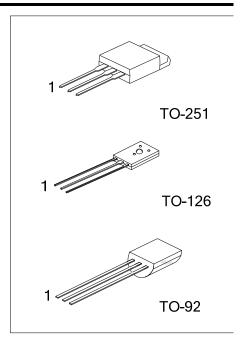
DESCRIPTION

The UTC 13003DW is a silicon NPN power switching transistor; it uses UTC's advanced technology to provide customers high collector-base breakdown voltage and high reliability, etc.

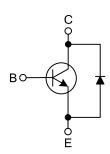
The UTC 13003DW is suitable for electronic ballast power switch circuit and low voltage electronic energy-saving light.

FEATURES

- * High collector-base breakdown voltage
- * High reliability



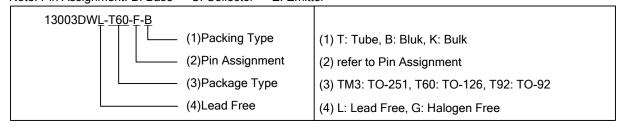
EQUIVALENT CIRCUIT



ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
13003DWL-x-TM3-T	13003DWG-x-TM3-T	TO-251	В	С	Е	Tube	
13003DWL-x-T60-F-K	13003DWG-x-T60-F-K	TO-126	В	С	Е	Bulk	
13003DWL-x-T92-A-B	13003DWG-x-T92-A-B	TO-92	Е	С	В	Tape Box	
13003DWL-x-T92-A-K	13003DWG-x-T92-A-K	TO-92	Е	С	В	Bulk	

Note: Pin Assignment: B: Base C: Collector E: Emitter



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■ MARKING

PACKAGE	MARKING		
TO-251	UTC 13003DW□ □□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□		
TO-126	UTC ☐ □□□□ → Pin Code Data Code 13003DW □ L: Lead Free G: Halogen Free		
TO-92	UTC 13003DW□ L: Lead Free G: Halogen Free Pin Code 1		

■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	350	V
Collector-Emitter Voltage		V_{CEO}	200	V
Emitter-Base Voltage		V_{EBO}	9	V
Continuous Collector Current		Ic	2	Α
Power Dissipation	T _A =25°C	P _D	1	W
	T _C =25°C		35	W
Junction Temperature		TJ	150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =1mA	350			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =10mA	200			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =1mA	9			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =350V, I _E =0			0.1	mA
Collector-Emitter Cut-Off Current	I _{CEO}	V _{CE} =200V, I _B =0			0.1	mA
Emitter-Base Cut-Off Current	I _{EBO}	V _{EB} =9V, I _C =0			0.1	mA
DC Current Gain (Note 1)	h _{FE}	I _C =0.5A, V _{CE} =5.0V	15		30	
Low ourrent and high ourrent by he ratio	h _{FE1} / h _{FE2}	h _{FE1} : V _{CE} =5V, I _C =50mA	0.7	0.9		
Low current and high current h _{FE2} h _{FE1} ratio		h _{FE2} : V _{CE} =5V, I _C =0.5A		0.9		
Collector-Emitter Saturation Voltage (Note)	V _{CE(SAT)}	I _C =1.5A, I _B =0.5A		0.21	1	V
Base-Emitter Saturation Voltage (Note)	$V_{BE(SAT)}$	I _C =1.5A, I _B =0.5A		1.1	1.5	V
Storage Time	ts		2.5		4.5	μs
Rise Time	t _R	UI9600, I _C =0.1A			1	μs
Fall Time	t⊧				1	μs
Transition Frequency	f _T	I _C =0.2A, V _{CE} =10V, f=1MHz	4			MHz
Diode Forward Voltage	V _F	I _F =2A			2.5	V

Note: Pulse test, pulse width tp≤300µs, Duty cycle≤2%

■ CLASSIFICATION OF h_{FE}

RANK	A	В	С
RANGE	15 ~ 20	20 ~ 25	25 ~ 30

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